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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/021,012	12/19/2001	Masahiro Yasukawa	040076.01	9786

25944 7590 11/06/2002

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EXAMINER
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QI, ZHI QIANG

ART UNIT	PAPER NUMBER
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2871

DATE MAILED: 11/06/2002

Please find below and/or attached an Office communication concerning this application or proceeding.

**Office Action Summary**

Application No.

10/021,012

Applicant(s)

YASUKAWA, MASAHIRO

Examiner

Mike Qi

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-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

**Period for Reply**

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133).
- Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

**Status**

- 1) ☒ Responsive to communication(s) filed on 22 August 2002.
- 2a) ☐ This action is **FINAL**.                      2b) ☒ This action is non-final.
- 3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

**Disposition of Claims**

- 4) ☒ Claim(s) 1-13 is/are pending in the application.
- 4a) Of the above claim(s) \_\_\_\_\_ is/are withdrawn from consideration.
- 5) ☒ Claim(s) 7, 12 and 13 is/are allowed.
- 6) ☒ Claim(s) 1-6 and 8-11 is/are rejected.
- 7) ☐ Claim(s) \_\_\_\_\_ is/are objected to.
- 8) ☐ Claim(s) \_\_\_\_\_ are subject to restriction and/or election requirement.

**Application Papers**

- 9) ☐ The specification is objected to by the Examiner.
- 10) ☐ The drawing(s) filed on \_\_\_\_\_ is/are: a) ☐ accepted or b) ☐ objected to by the Examiner.
- Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).
- 11) ☐ The proposed drawing correction filed on \_\_\_\_\_ is: a) ☐ approved b) ☐ disapproved by the Examiner.
- If approved, corrected drawings are required in reply to this Office action.
- 12) ☐ The oath or declaration is objected to by the Examiner.

**Priority under 35 U.S.C. §§ 119 and 120**

- 13) ☒ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
- a) ☒ All    b) ☐ Some    c) ☐ None of:
1. ☐ Certified copies of the priority documents have been received.
2. ☒ Certified copies of the priority documents have been received in Application No. 08/955,461.
3. ☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).
- \* See the attached detailed Office action for a list of the certified copies not received.
- 14) ☐ Acknowledgment is made of a claim for domestic priority under 35 U.S.C. § 119(e) (to a provisional application).
- a) ☐ The translation of the foreign language provisional application has been received.
- 15) ☐ Acknowledgment is made of a claim for domestic priority under 35 U.S.C. §§ 120 and/or 121.

**Attachment(s)**

- 1) ☒ Notice of References Cited (PTO-892)                      4) ☐ Interview Summary (PTO-413) Paper No(s). \_\_\_\_\_
- 2) ☐ Notice of Draftsperson's Patent Drawing Review (PTO-948)                      5) ☐ Notice of Informal Patent Application (PTO-152)
- 3) ☐ Information Disclosure Statement(s) (PTO-1449) Paper No(s) \_\_\_\_\_                      6) ☐ Other: \_\_\_\_\_

## DETAILED ACTION

### *Claim Rejections - 35 USC § 103*

1. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

2. Claim 1 is rejected under 35 U.S.C. 103(a) as being unpatentable over US 5,767,827 (Kobayashi et al) in view of US 5,805,252 (Shimada et al).

Claim 1, Kobayashi discloses (col.4, lines 18–64; Fig.1) that a liquid crystal panel comprising:

- reflecting electrodes (9) formed on a substrate (1);
- a switching element (2,3,4) formed corresponding to each of the reflecting electrode (9);
- a passivation film (11) formed on the reflecting electrodes (9) is a silicon oxide film as a protective film for the pixel transistor on the pixel electrodes;
- insulating films (7a and 7b) (as an insulating interlayer) formed between the reflecting electrode (9) and a capacitance electrode (20) (the capacitance electrode must be made of a metal, also the data line '8' and the drain electrode '23' must made of metal) above the switching element (2,3,4).

Although Kobayashi does not expressly disclose the insulating film is silicon

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nitride film, but a dielectric film as an insulating film made of silicon nitride or silicon oxide was common and known in the art, such as Shimada disclosed (col.1, line 67- col.2, line 1) that an insulating film is made of silicon nitride or silicon oxide.

Therefore, it would have been obvious to those skilled in the art at the time the invention was made to use silicon nitride film as claimed in claim 1 for achieving the insulation and the insulating effect having moisture resistance.

3. Claim 2 is rejected under 35 U.S.C. 103(a) as being unpatentable over Kobayashi and Shimada as applied to claim 1 above, and further in view of US 5,056,895 (Kahn).

Claim 2, Kahn discloses (col.4, line 51 – col.6, line 66; Fig.1) that a liquid crystal panel substrate comprising a semiconductor substrate (40) and is then covered with a silicon dioxide dielectric insulating layer (50), and an additional oxide layer (53) covers the first oxide layer, and both of them are between the electrode (70) (composed of Au 'gold', so that must be reflective electrode) and the drain electrode (44) (the drain electrode must be a conductive metal material). Therefore, the insulating interlayer (50,53) has a laminate structure. Kahn also indicates (col.5, lines 40-42) that the composition of oxide layer 50,53,64,68, is well known in the art, and is preferably either SiO<sub>2</sub>, or Si<sub>3</sub>N<sub>4</sub>. Therefore, the insulating layer (53) using silicon nitride film and the insulating layer (50) using silicon oxide film would have been obvious, and using dielectric films having different optical density would have dielectric mirror effect to increase the reflectance.

Therefore, it would have been obvious to those skilled in the art at the time the invention was made to use laminated insulating films as claimed in claim 2 for increasing the reflectance.

4. Claims 3, 8-9 are rejected under 35 U.S.C. 103(a) as being unpatentable over Us 5,510,918 (Matsunaga et al) in view of US 5,056,895 (Kahn).

Claim 3, Matsunaga discloses (col.4, line 12 – col.5, line 32; Figs.1,8) that a liquid crystal display comprising a periphery region of the pixel region on the substrate (SUB1) having gate terminal (GTM) and drain terminal (DTM) (the terminal must be made of metal) and insulating layer (GI), such that the periphery region having metal layer and insulation interlayer. Matsunaga also discloses (col.7, line 62 – col.8, line 20; Fig.8) that a liquid crystal display comprising a passivation film (PSV1) made from silicon nitride film formed at the periphery region, i.e., a passivation film formed on the edge section of the metal layer and the insulating interlayer, and the passivation film having a high passivation effect in the peripheral portion against the humidity or the like, such as moisture resistance. *side*

Matsunaga does not expressly disclose a pixel region having a matrix of reflecting electrodes, and a passivation film having a laminate structure.

However, a reflection type liquid crystal display having reflecting electrode was common and known in the art as using ambient light and reducing power consumption.

Kahn discloses (col.4, line 51 – col.6, line 66; Fig.1) that a liquid crystal panel substrate comprising a semiconductor substrate (40) and is then covered with a silicon dioxide dielectric insulating layer (50), and an additional oxide layer (53) covers

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the first oxide layer, and both of them are between the electrode (70) (composed of Au 'gold', so that must be reflective electrode) and the drain electrode (44) (the drain electrode must be a conductive metal material). Therefore, the insulating interlayer (50,53) has a laminate structure. Kahn also indicates (col.5, lines 40-42) that the composition of oxide layer 50,53,64,68, is well known in the art, and is preferably either  $\text{SiO}_2$ , or  $\text{Si}_3\text{N}_4$ . Therefore, the insulating layer (53) using silicon nitride film and the insulating layer (50) using silicon oxide film would have been obvious, and using dielectric films having different optical density would have dielectric mirror effect to increase the reflectance.

Therefore, it would have been obvious to those skilled in the art at the time the invention was made to use reflecting electrodes and the passivation film (also is an insulating film) as claimed in claim 3 for reducing power consumption and increasing the reflectance.

Claim 8, Matsunaga discloses (Fig.8) that a seal material (SL) formed on the passivation film (PSV1) (silicon nitride film) for sealing with a counter substrate (SUB2).

Claim 9, inherently, the edge section is a scribed region of the substrate to form the periphery region, and that was a common and known in the art for more precisely forming a periphery region making a scribed region on the substrate.

5. Claim 4 is rejected under 35 U.S.C. 103(a) as being unpatentable over 5,767,827 (Kobayashi et al) in view of US 5,510,918 (Matsunaga et al).

Claim 4, Kobayashi discloses (col.4, lines 18-64; Fig.1) that a liquid crystal panel comprising:

- reflecting electrodes (9) formed on a substrate (1) and a transistor formed corresponding the each of the reflecting electrodes;
- a drive circuit for scanning the signals formed around the display pixel area (a peripheral circuit arranged in a periphery region of the pixel region on the substrate for supplying signal to the transistors in the pixel region); <sup>(col. 3, lines 5-6)</sup>
- a passivation film comprising a silicon oxide film (11) formed on the reflecting electrodes (9) in the pixel region.

Kobayashi does not expressly disclose that a second passivation film comprising a silicon nitride film formed <sup>(side edge section of)</sup> on the periphery region.

However, Matsunaga discloses (Figs. 7,8) that a passivation film (PSV1) (silicon nitride film) formed on the periphery region, and the passivation film (PSV1) having a high passivation effect for protecting the transistor against humidity.

Therefore, it would have been obvious to those skilled in the art at the time the invention was made to arrange a passivation film on the periphery region as claimed in claim 4 for achieving humidity resistant.

6. Claim 5 is rejected under 35 U.S.C. 103(a) as being unpatentable over <sup>and Matsunaga</sup> Kobayashi as applied to claim 4 above, and further in view of US 5,805,252 (Shimada et al).

Claim 5, Kobayashi discloses (col.4, lines 18-64; Fig.1) that insulating film (7a, 7b) provided between the reflecting electrode (9) and a capacitance electrode (20) (the capacitance electrode must be made of a metal), so that is an insulating interlayer provided between the reflecting electrode and a metal layer.

Although Kobayashi does not expressly disclose the insulating interlayer is a silicon nitride film, but as an insulating layer made of silicon nitride was common and known in the art as the silicon nitride having insulation property. Such as Shimada discloses (col.1, line 67-col.2, line 1) that an insulating film is made of silicon nitride or silicon oxide, and that would have been at least obvious.

7. Claim 6 is rejected under 35 U.S.C. 103(a) as being unpatentable over Kobayashi <sup>and Matsunaga</sup> as applied to claim 4 above, and further in view of US 5,056,895 (Kahn).

Claim 6, Kahn discloses (col.4, line 51 – col.6, line 66; Fig.1) that a liquid crystal panel substrate comprising a semiconductor substrate (40) and is then covered with a silicon dioxide dielectric insulating layer (50), and an additional oxide layer (53) covers the first oxide layer, and both of them are between the electrode (70) (composed of Au 'gold', so that must be reflective electrode) and the drain electrode (44) (the drain electrode must be a conductive metal material). Therefore, the insulating interlayer (50,53) has a laminate structure. Kahn also indicates (col.5, lines 40-42) that the composition of oxide layer 50,53,64,68, is well known in the art, and is preferably either  $\text{SiO}_2$ , or  $\text{Si}_3\text{N}_4$ . Therefore, the insulating layer (53) using silicon nitride film and the insulating layer (50) using silicon oxide film would have been obvious, and using dielectric films having different optical density would have dielectric mirror effect to increase the reflectance.

Therefore, it would have been obvious to those skilled in the art at the time the invention was made to use laminated insulating films as claimed in claim 6 for increasing the reflectance.



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8. Claims 10-11 are rejected under 35 U.S.C. 103(a) as being unpatentable over US 5,510,918 (Matsunaga et al) in view of US 5,056,895 (Kahn).

Claim 10, Matsunaga discloses (col.7, line 62 – col.8, line 20; Fig.8) that a liquid crystal display comprising a passivation film (PSV1) made from silicon nitride film <sup>side edge</sup> formed at the periphery region, i.e., a passivation film formed on the edge region (scribed region) of a substrate, and the passivation film having a high passivation effect in the peripheral portion against the humidity or the like.

Although Matsunaga does not expressly disclose a pixel region having reflecting electrodes, but as a reflection type liquid crystal display having reflecting electrode was common and known in the art as using ambient light and reducing power consumption. Matsunaga does not expressly disclose using semiconductor substrate. However, Kahn discloses (col.5, lines 1-8) that semiconductor substrate (40) is suitable for standard integrated circuit processes that are well known in the art, and that conventional processes, well known in the art, can be used to fabricate MOS transistors, and by using conventional integrated circuit techniques, the cells can be fabricated singly or in multiples on the silicon wafer.

Therefore, it would have been obvious to those skilled in the art at the time the invention was made to use reflecting electrodes and semiconductor substrate as claimed in claim 10 for reducing power consumption and using the standard processes to fabricate the cells.

Claim 11, Kahn discloses (col.4, line 51 – col.6, line 66; Fig.1) that a

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liquid crystal panel substrate comprising a semiconductor substrate (40) and is then covered with a silicon dioxide dielectric insulating layer (50), and an additional oxide layer (53) covers the first oxide layer, and both of them are between the electrode (70) (composed of Au 'gold', so that must be reflective electrode) and the drain electrode (44) (the drain electrode must be a conductive metal material). Therefore, the insulating interlayer (50,53) has a laminate structure. Kahn also indicates (col.5, lines 40-42) that the composition of oxide layer 50,53,64,68, is well known in the art, and is preferably either  $\text{SiO}_2$ , or  $\text{Si}_3\text{N}_4$ . Therefore, the insulating layer (53) using silicon nitride film and the insulating layer (50) using silicon oxide film would have been obvious, and using dielectric films having different optical density would have dielectric mirror effect to increase the reflectance.

Therefore, it would have been obvious to those skilled in the art at the time the invention was made to use the passivation film having a laminate structure as claimed in claim 11 for increasing the reflectance.

### ***Allowable Subject Matter***

9. Claims 7 and 12-13 are allowed.

The prior art of record neither discloses nor teaches that a liquid crystal display panel comprising various elements, more specifically, as the following:

a first passivation film comprising a first silicon oxide film formed in the pixel region; and a second passivation film having a laminate structure comprising a second silicon oxide film and a silicon nitride film formed on the second silicon oxide film, the

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second passivation film being formed at edge section of the metal layer and the insulating interlayer [claim 7];

the passivation film extending on a scribed region (edge region) of the first substrate [claim 12].

The closest references US 5,056,895 (Kahn) and US 5,510,918 (Matsunaga et al) disclose that a liquid crystal display comprising passivation film having laminate structure formed on a reflecting electrode and a passivation film formed on the edge portion, but they do not disclose the second passivation film having laminate structure formed at edge section of the metal layer and the insulating interlayer and the <sup>as shown in Fig. 4</sup> passivation film extending on a scribed region (edge region) of the first substrate as shown in Fig.4.

### ***Response to Arguments***

10. Applicant's arguments with respect to claims 1-6 and 8-13 have been considered but are moot in view of the new ground(s) of rejection.

### ***Conclusion***

11. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure.

12. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Mike Qi whose telephone number is (703) 308-6213.

The examiner can normally be reached on 349.

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If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, William Sikes can be reached on (703) 308-4842. The fax phone numbers for the organization where this application or proceeding is assigned are (703) 308-7721 for regular communications and (703) 308-7721 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 308-0956.

Mike Qi  
October 16, 2002

  
TOANTON  
PRIMARY EXAMINER